

Silicon PNP Power Transistors

2SA715

DESCRIPTION

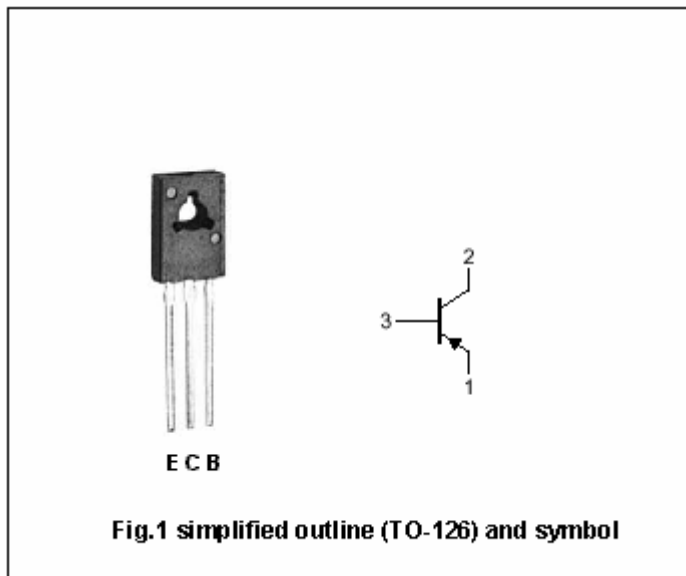
- With TO-126 package
- Complement to type 2SC1162

APPLICATIONS

- Low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute Maximun Ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-35	V
V _{CEO}	Collector-emitter voltage	Open base	-35	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-2.5	A
I _{CM}	Collector current-Peak		-3	A
P _C	Collector power dissipation	T _a =25°C	0.75	W
		T _C =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; R _{BE} =∞	-35			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA; I _E =0	-35			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2.0A; I _B =-0.2A(Pulse test)		-0.5	-1.0	V
V _{BE}	Base-emitter voltage	I _C =-1.5A; V _{CE} =-2V(Pulse test)		-1.0	-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-35V; I _E =0			-20	μA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-2V	60		320	
h _{FE-2}	DC current gain	I _C =-1.5A; V _{CE} =-2V(Pulse test)	20			
f _T	Transition frequency	I _C =-0.2A; V _{CE} =-2V(Pulse test)		160		MHz

◆ h_{FE-1} Classifications

B	C	D
60-120	100-200	160-320

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PACKAGE OUTLINE

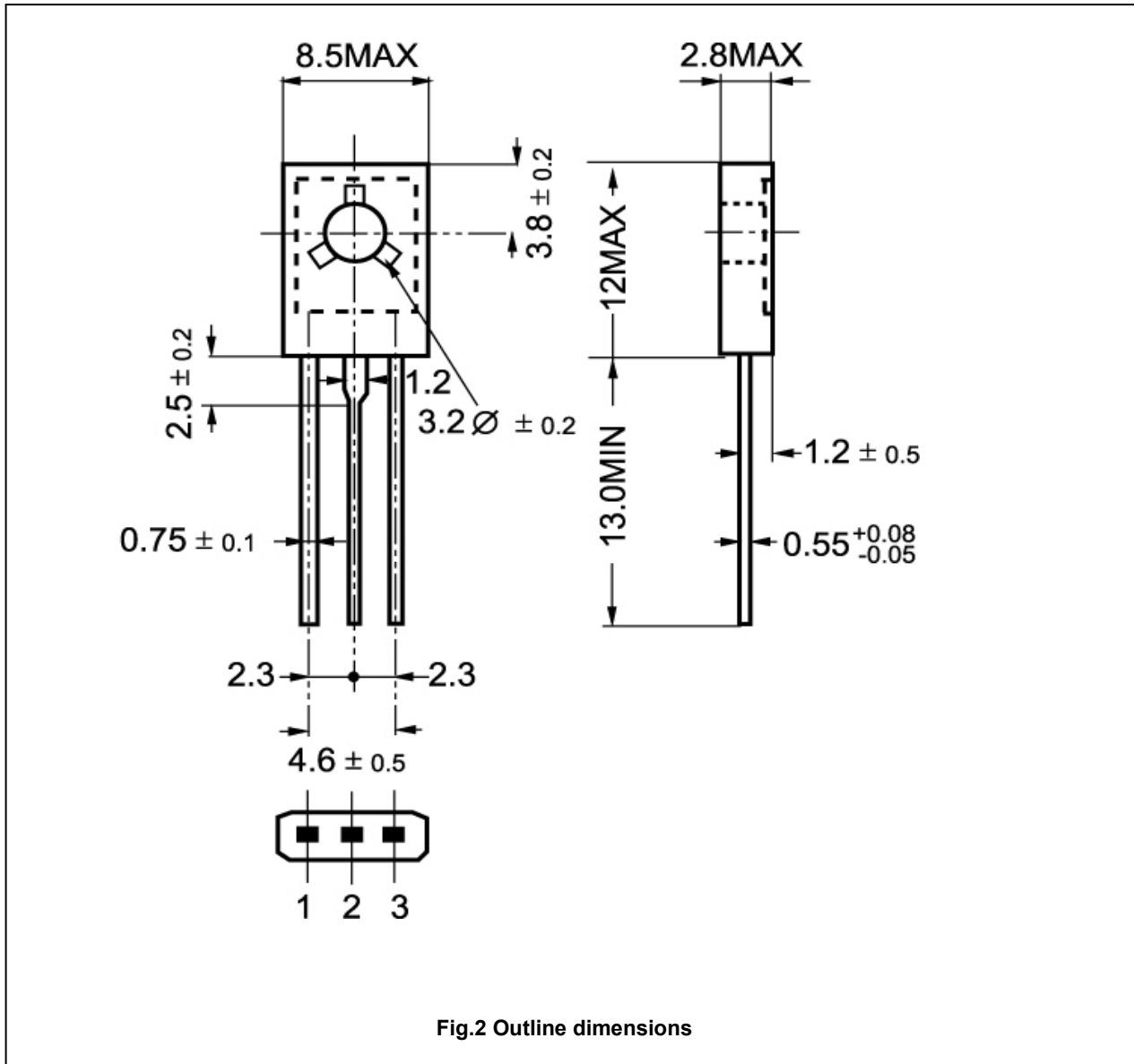


Fig.2 Outline dimensions

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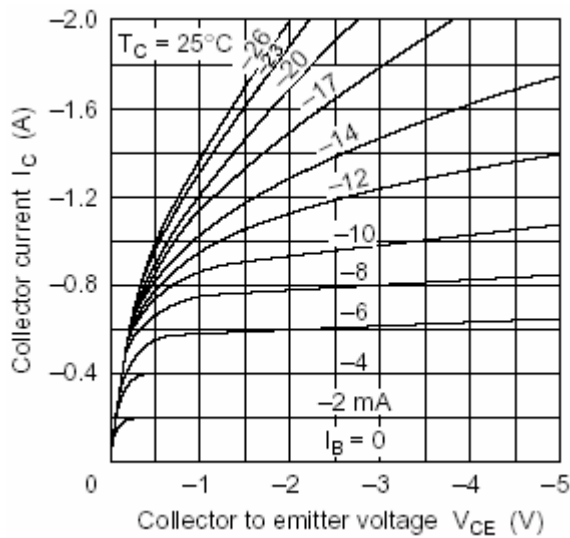


Fig.3 Static Characteristic

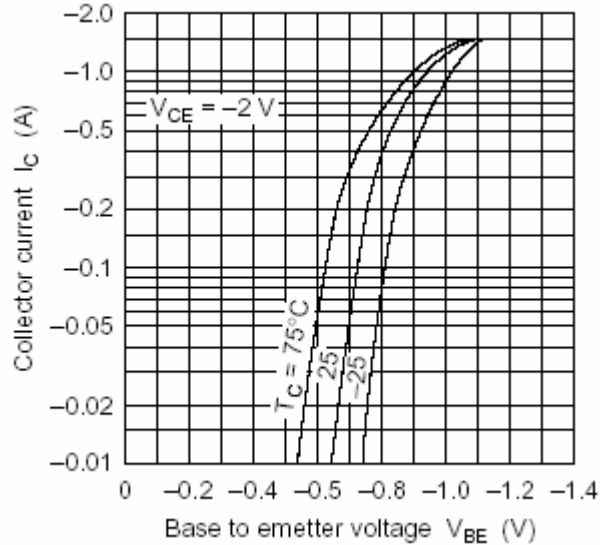


Fig.4 Base-Emitter On Voltage

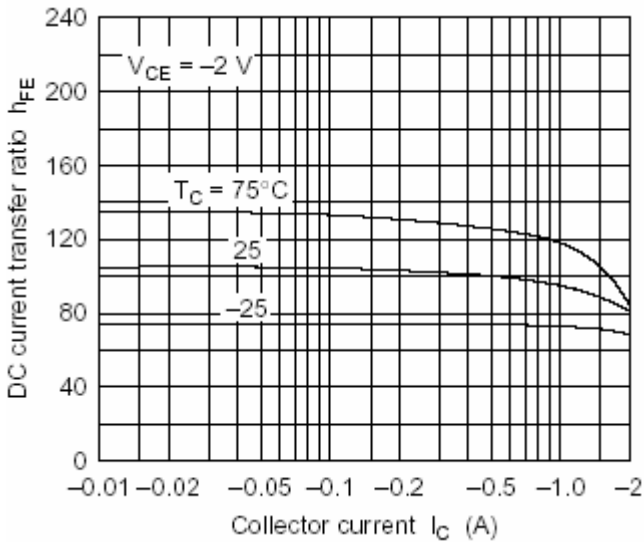


Fig.5 DC current Gain

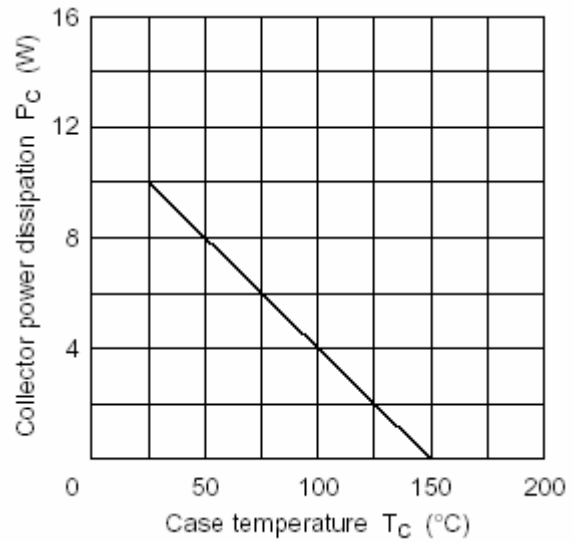


Fig.6 Power Derating

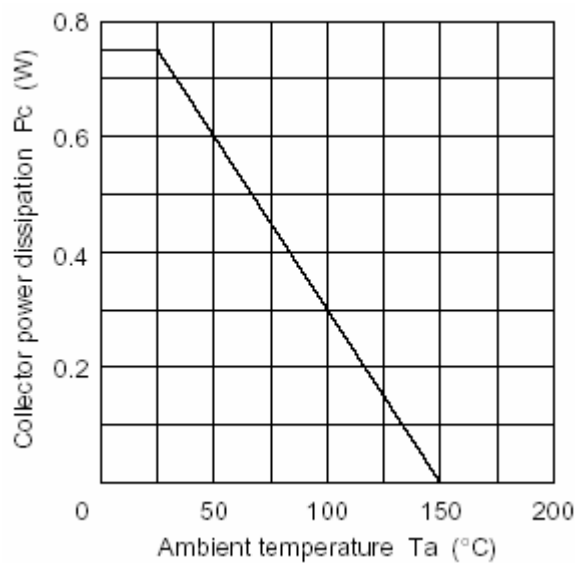


Fig.7 Power Derating

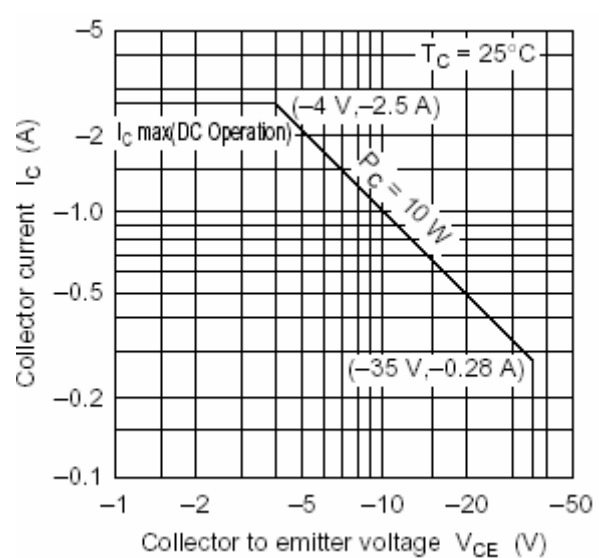


Fig.8 Safe Operating Area